

vaporizing the raw material for the thin film from the liquid so as to be fed to one of a part and a plurality of parts of a surface to form the thin film so as to form the thin film with a predetermined pattern over the surface to form the thin film.

2. (Amended) The method for forming a thin film according to Claim 1, further including using a surface of the substrate as a surface to place the liquid, and forming the thin film in a region other than the region in which the liquid is placed on the surface to place the liquid.

3. (Amended) The method for forming a thin film according to Claim 1, further including placing a first substrate to place the liquid and a second substrate to form the thin film so that the surface to place the liquid of the first substrate faces the surface to form the thin film of the second substrate, and vaporizing the raw material for the thin film from the liquid placed on one of a part and a plurality of parts of the first substrate so as to be fed to the surface to form the thin film of the second substrate.

4. (Amended) The method for forming a thin film according to Claim 3, further including heating the surface to form the thin film of the second substrate to a temperature at which a vaporized substance of the raw material for the thin film is decomposable, and heating the first substrate to a temperature at which the raw material for the thin film is vaporized from the liquid by the heat radiated from the second substrate.

5. (Twice Amended) The method for forming a thin film according to Claim 1, further including, before the step of placing the liquid, forming an active region and an inactive region for the chemical vapor deposition in the surface to form the thin film so that the thin film is selectively deposited.

6. (Amended) The method for forming a thin film according to Claim 5, further including performing the formation of the active region and the inactive region for the chemical vapor deposition by forming a self-assembled film on the surface to form the thin

film having hydroxyl groups using a silane derivative represented by a general formula RSiX_3 (wherein R is a fluoroalkyl group in which terminal hydrogen of the alkyl group is replaced with fluorine, and X is an alkoxy group or halogen group); and performing ultraviolet irradiation on the self-assembled film through a photomask or performing electron beam irradiation on necessary parts of the self-assembled film so that the self-assembled film in a region to form the active region for the chemical vapor deposition is removed.

7. (Twice Amended) The method for forming a thin film according to Claim 1, further including performing the step of vaporizing the raw material for the thin film while supplying inert gas, hydrogen gas, or a mixture of inert gas and hydrogen gas parallel to the surface to place the liquid of the substrate.

8. (Twice Amended) The method for forming a thin film according to Claim 1, further including performing the step of placing the liquid by an ink-jet method.

9. (Amended) An electronic apparatus, comprising:
the thin film formed by the method according to claim 1, the thin film being used as an electrode.

REMARKS

Claims 1-9 are pending. By this Preliminary Amendment, the Abstract and specification are replaced with a Substitute Abstract and Substitute Specification, and claims 1-9 are amended.

The attached Appendix includes marked-up copies of the specification (37 C.F.R. §1.125(b)(2)) and each rewritten claim (37 C.F.R. §1.121(c)(1)(ii)).